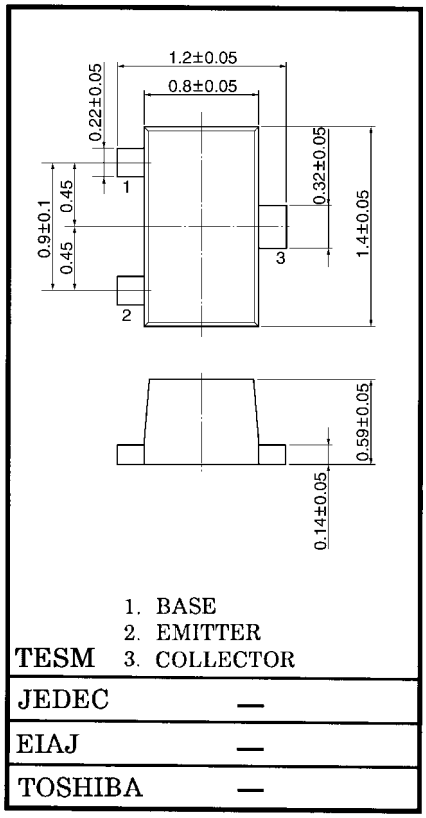
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

RN2107FT, RN2108FT, RN2109FT

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

- High-density mount is possible because of devices housed in very thin TESM packages.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Wide range of resistor values are available to use in various circuit designs.
- Complementary to RN1107FT, RN1108FT, RN1109FT

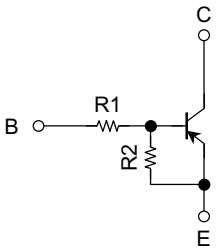
Unit in mm



1. BASE
2. EMITTER
3. COLLECTOR

TESM	
JEDEC	—
EIAJ	—
TOSHIBA	—

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2107FT	10	47
RN2108FT	22	47
RN2109FT	47	22

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage	RN2107FT~2109FT	V_{CBO}	−50	V
Collector-emitter voltage		V_{CEO}	−50	V
Emitter-base voltage	RN2107FT	V_{EBO}	−6	V
	RN2108FT		−7	
	RN2109FT		−15	
Collector current	RN2107FT~2109FT	I_C	−100	mA
Collector power dissipation		P_C	100	mW
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55~150	°C

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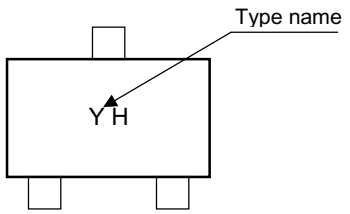
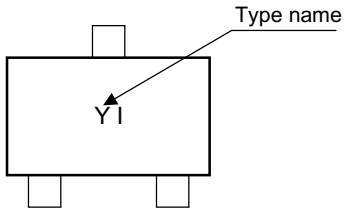
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2107FT~2109FT	I_{CBO}	V_{CB} = –50 V, I_E = 0	—	—	–100	nA
		I_{CEO}	V_{CE} = –50 V, I_B = 0	—	—	–500	
Emitter cut-off current	RN2107FT	I_{EBO}	V_{EB} = –6 V, I_C = 0	–0.081	—	–0.15	mA
	RN2108FT		V_{EB} = –7 V, I_C = 0	–0.078	—	–0.145	
	RN2109FT		V_{EB} = –15 V, I_C = 0	–0.167	—	–0.311	
DC current gain	RN2107FT	h_{FE}	V_{CE} = –5 V, I_C = –10 mA	80	—	—	
	RN2108FT			80	—	—	
	RN2109FT			70	—	—	
Collector-emitter saturation voltage	RN2107FT~2109FT	$V_{CE\ (sat)}$	I_C = –5 mA, I_B = –0.25 mA	—	–0.1	–0.3	V
Input voltage (ON)	RN2107FT	$V_{I\ (ON)}$	V_{CE} = –0.2 V, I_C = –5 mA	–0.7	—	–1.8	V
	RN2108FT			–1.0	—	–2.6	
	RN2109FT			–2.2	—	–5.8	
Input voltage (OFF)	RN2107FT	$V_{I\ (OFF)}$	V_{CE} = –5 V, I_C = –0.1 mA	–0.5	—	–1.0	V
	RN2108FT			–0.6	—	–1.16	
	RN2109FT			–1.5	—	–2.6	
Transition frequency	RN2107FT~2109FT	f_T	V_{CE} = –10 V, I_C = –5 mA	—	200	—	V
Collector output capacitance	RN2107FT~2109FT	C_{ob}	V_{CB} = –10 V, I_E = 0, f = 1 MHz	—	3	6	pF
Input resistor	RN2107FT	R1	—	7	10	13	kΩ
	RN2108FT			15.4	22	28.6	
	RN2109FT			32.9	47	61.1	
Resistor ratio	RN2107FT	R1/R2	—	0.919	0.213	0.232	
	RN2108FT			0.421	0.468	0.515	
	RN2109FT			1.92	2.14	2.35	

Type Name	Marking
RN1107FT	
RN1108FT	
RN1109FT